ELECTRONICS, INC.
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1N485B & 1N486B
Small Signal Diode

Features:

- DO–35 Package

Absolute Maximum Ratings: (T_A = +25°C, Note 1 unless otherwise specified)

Max. Repetitive Reverse Voltage, V_{RRM}
- 1N485B 200V
- 1N486B 250V

Power Dissipation, P_D 500mW

Average Rectified Forward Current, $I_{F(AV)}$ 200mA

None–Repetitive Forward Surge Current, I_{FSM}
- Pulse Width = 10.0 seconds 1.0A
- Pulse Width = 1.0 microsecond 4.0A

Operating Junction Temperature, T_J . . . . . 175°C

Storage Temperature Range, T_{stg} . . . . . –65° to +200°C

Thermal Resistance, Junction to Ambient, R_{thJA} . . . . . +300°C/W

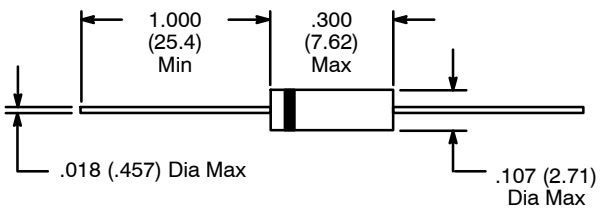
Note 1. These ratings are limiting values above which the serviceability of the device may be impaired.

Note 2. These ratings are based on a maximum junction temperature of +200°C.

Note 3. These are steady state limits.

Electrical Characteristics: (T_A = +25°C, unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Breakdown Voltage 1N485B	V_R	I_R = 5μA	200	–	–	V
1N486B		I_R = 100μA	250	–	–	V
Forward Voltage	V_F	I_F = 100mA	–	–	1.0	V
Reverse Leakage 1N485B	I_R	V_R = 175V	–	–	25	μA
		V_R = 175V, T_A = 150°C	–	–	5	μA
1N486B	I_R	V_R = 225V	–	–	50	μA
	I_R	V_R = 225V, T_A = 150°C	–	–	10	μA



Color Band Denotes Cathode